60 V, single N-channel Trench MOSFET

6 August 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected

3. Applications

- · Relay driver
- High-speed line driver
- · Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	300	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	190	mA
Static chara	cteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C		-	3	4.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002AK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX7002AK	%CM

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	٧
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	300	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	190	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	120	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	760	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		-	1330	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	ain diode			'		,
I _S	source current	T _{amb} = 25 °C	[1]	-	190	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

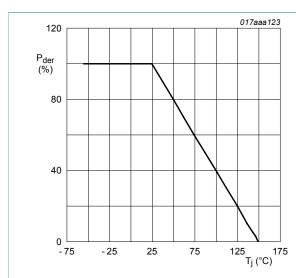


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

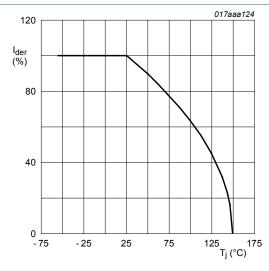


Fig. 2. Normalized continuous drain current as a function of junction temperature

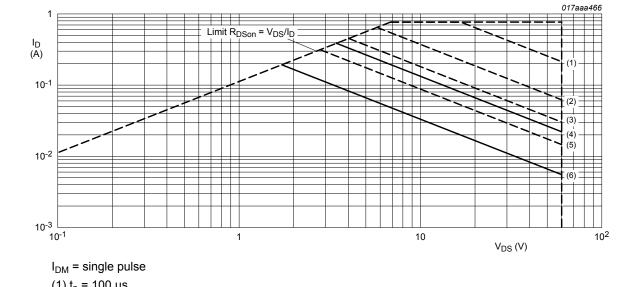
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100~\%$$

NX7002AK

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- (1) $t_p = 100 \ \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; T_{sp} = 25 °C
- $(5) t_p = 100 \text{ ms}$
- (6) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	410	470	K/W
			[2]	-	330	380	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	95	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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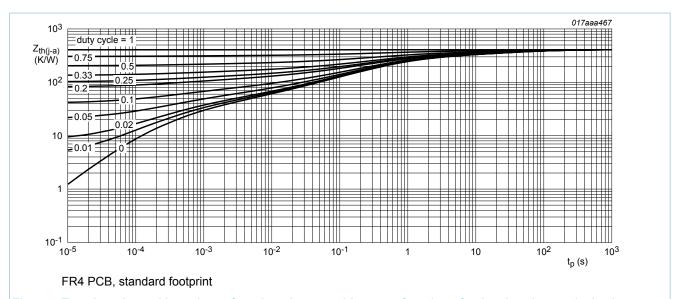


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

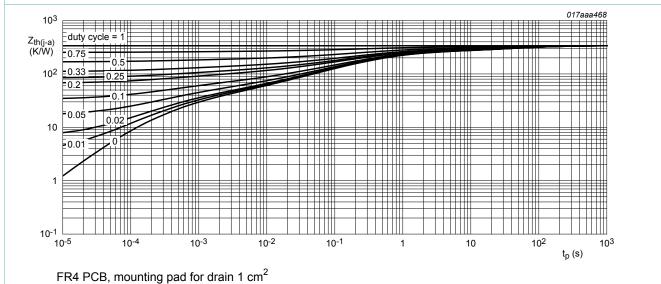


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					_
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.5	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C	-	3	4.5	Ω
		V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	6.2	9.2	Ω
		V _{GS} = 5 V; I _D = 100 mA; T _j = 25 °C	-	3.7	5.2	Ω
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	500	-	mS
Dynamic c	haracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 200 mA; V_{GS} = 4.5 V;	-	0.33	0.43	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	15	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.4	-	pF
C _{rss}	reverse transfer capacitance		-	2	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_{L} = 250 Ω ; V_{GS} = 10 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	11	20	ns
t _f	fall time		-	5	-	ns
Source-dra	ain diode		1	1	-1	
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.8	1.2	V

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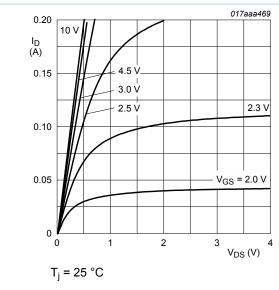


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

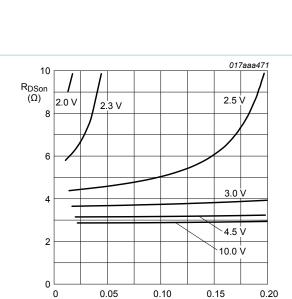
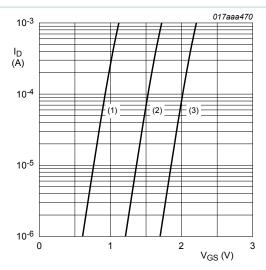


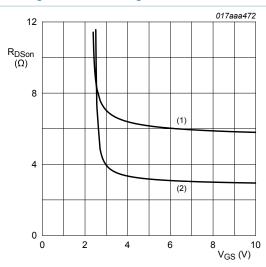
Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 T_j = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

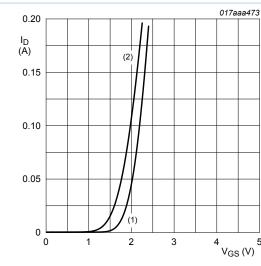
(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

T_i = 25 °C

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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_j = 25 \, ^{\circ}C$

(2) $T_i = 150 \, ^{\circ}C$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

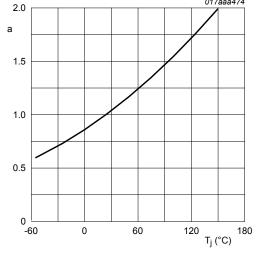
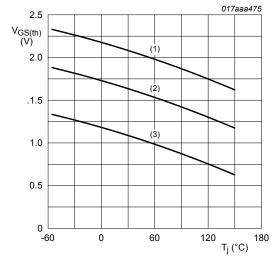


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

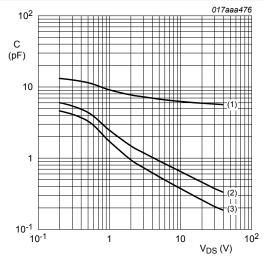
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 I_D = 0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- $(1) C_{iss}$
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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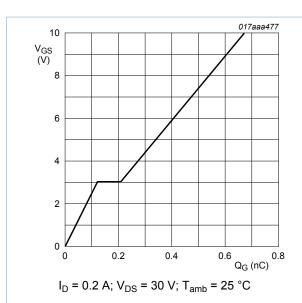


Fig. 14. Gate-source voltage as a function of gate charge; typical values

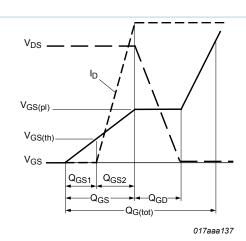
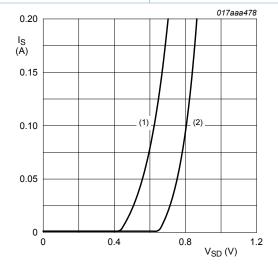


Fig. 15. MOSFET transistor: Gate charge waveform definitions



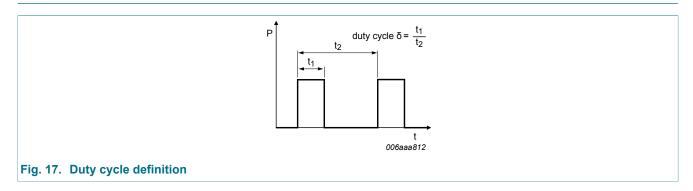
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

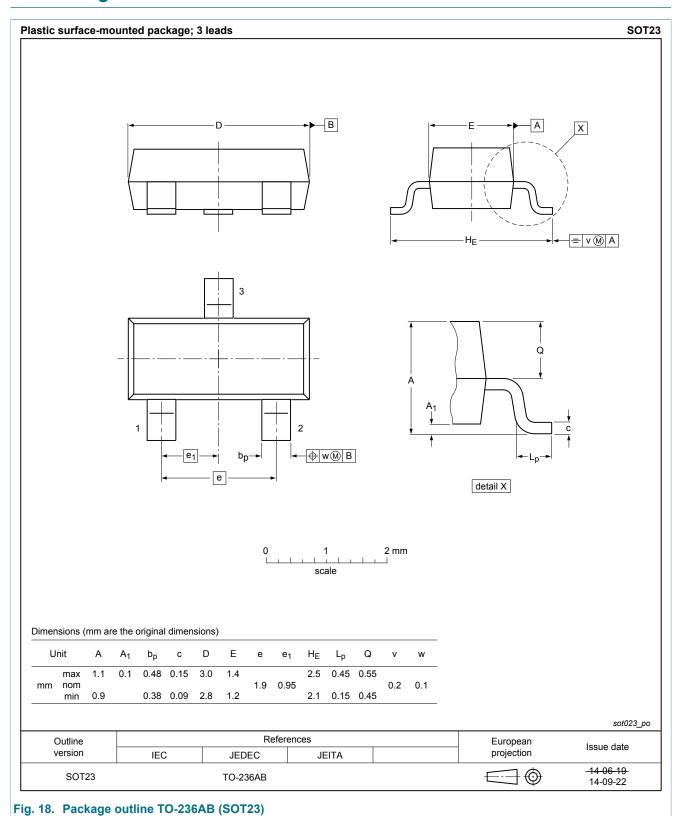
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11. Test information



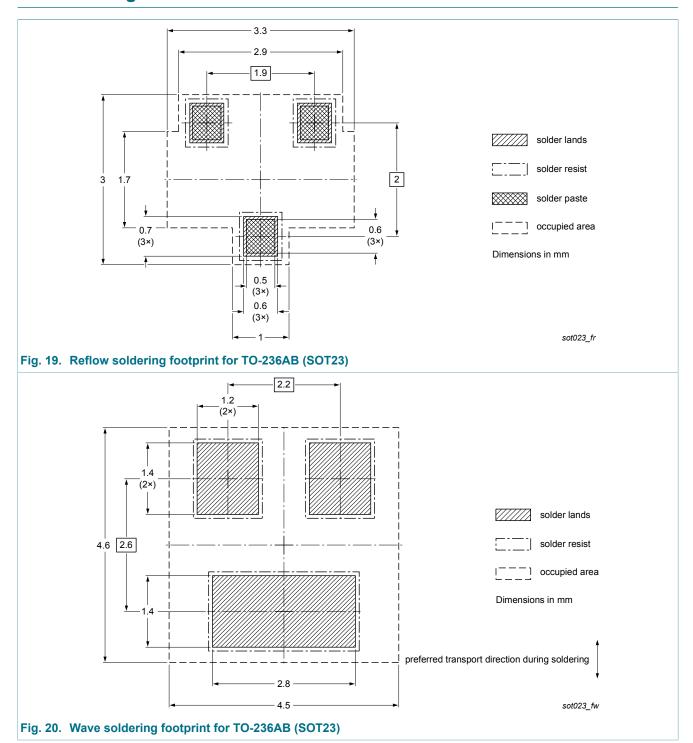
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AK v.7	20150806	Product data sheet	-	NX7002AK v.6
Modifications:	Dynamic paramete	rs updated		
NX7002AK v.6	20150521	Product data sheet	-	NX7002AK v.5
NX7002AK v.5	20130213	Product data sheet	-	NX7002AK v.4
NX7002AK v.4	20121213	Product data sheet	-	NX7002AK v.3
NX7002AK v.3	20120710	Product data sheet	-	NX7002AK v.2
NX7002AK v.2	20120301	Product data sheet	-	NX7002AK v.1
NX7002AK v.1	20120212	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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